

IN THE CLAIMS:

Please cancel claims 1 and 2 in their entirety without prejudice nor disclaimer of the subject matter set forth therein.

1. (Canceled)

2. (Canceled)

3. (Original) A method for manufacturing a semiconductor device, comprising the steps of:

forming a recess in an insulating film on a substrate;

depositing a first conductive film on a bottom and wall surface of the recess, the first conductive film being formed from a first copper alloy having oxidation resistance;

growing a second conductive film on the first conductive film by an electroplating method so as to completely fill the recess, the second conductive film being formed from copper or a second copper alloy; and

integrating the first and second conductive films into a third conductive film so as to form an embedded wiring of the third conductive film.

4. (Original) The method according to claim 3, wherein the step of depositing the first conductive film includes the step of depositing the first conductive film with (111) orientation with respect to the bottom of the recess.

5. (Original) The method according to claim 3, wherein the first copper alloy contains at least one of elements Al, Si, Zr and Ru.